

## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

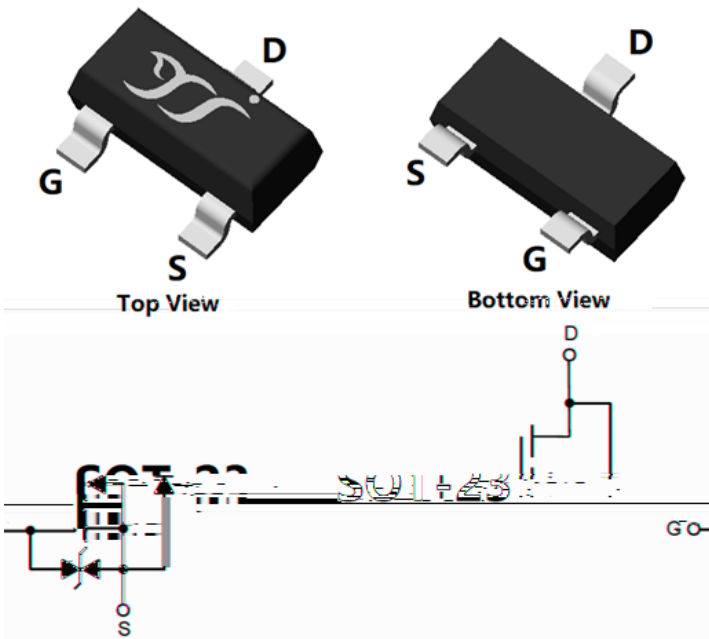
$V_{DS}$	60V
$I_D$	0.6A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	1.5
$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	1.8
$R_{DS(ON)}$ (at $V_{GS}=2.5V$ )	3.7
$R_{DS(ON)}$ (at $V_{GS}=1.8V$ )	8.5
Gate-Source ESD Rating Up to 2KV (HBM)	

### General Description

Trench Power MV MOSFET technology  
 Voltage controlled small signal switch  
 Low input Capacitance  
 Fast Switching Speed  
 Moisture Sensitivity Level 1  
 Epoxy Meets UL 94 V-0 Flammability Rating  
 Halogen Free

### Applications

Battery operated systems  
 Solid-state relays  
 Direct logic-level interface TTL/CMOS



### Absolute Maximum Ratings ( $T_A=25$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	60	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_A=25$	$I_D$	0.6	A
	$T_A=100$		0.38	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	1.5	A
Total Power Dissipation <sup>B</sup>	$T_A=25$	$P_D$	0.8	W
	$T_A=100$		0.3	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 +150	

### Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>C</sup>	Steady-State	$R_{JA}$	120	150	$^{\circ}W$

### Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
BSS138KJ	F2	BK	3000	30000	120000	7" reel



# BSS138KJ

## Electrical Characteristics ( $T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$	-	-	1	$\mu A$
		$V_{DS}=60V, V_{GS}=0V, T_J=150$	-	-	100	
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 10$	$\mu A$

Gate Threshold Voltage



## Typical Electrical and Thermal Characteristics Diagrams

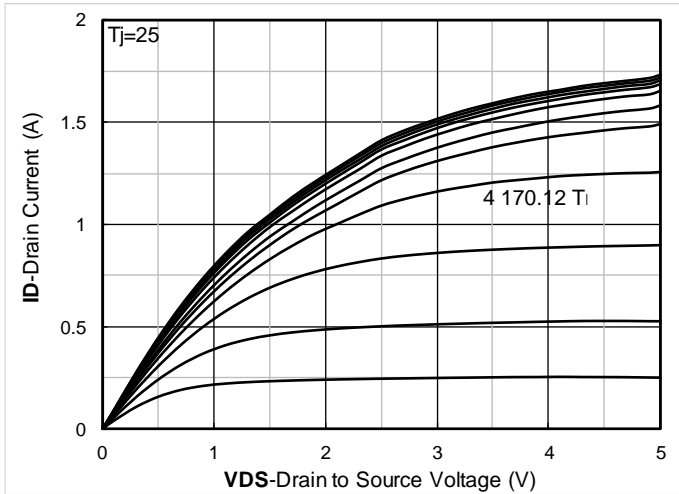


Figure 1. Output Characteristics

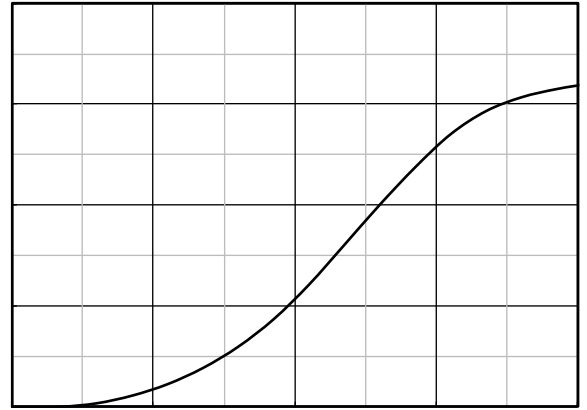


Figure 2. Transfer Characteristics



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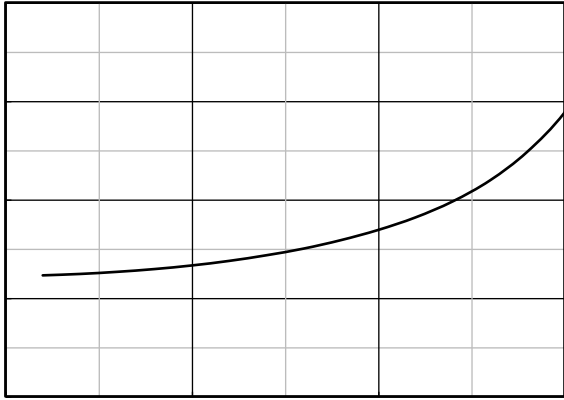


Figure 7.  $R_{DS(on)}$  VS Drain Current

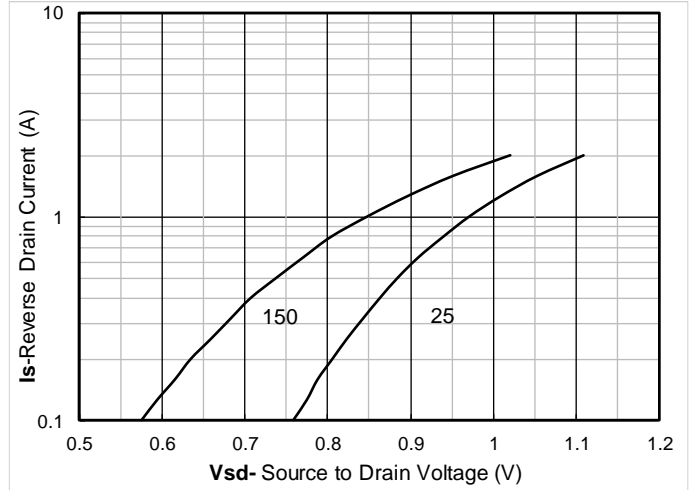


Figure 8. Forward characteristics of reverse diode

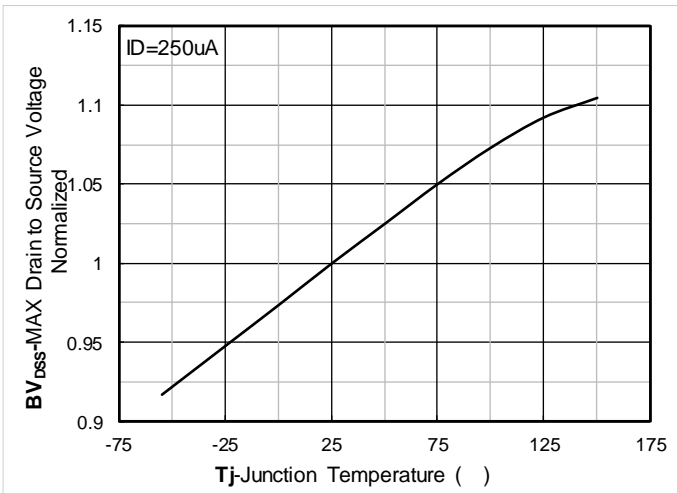


Figure 9. Normalized breakdown voltage

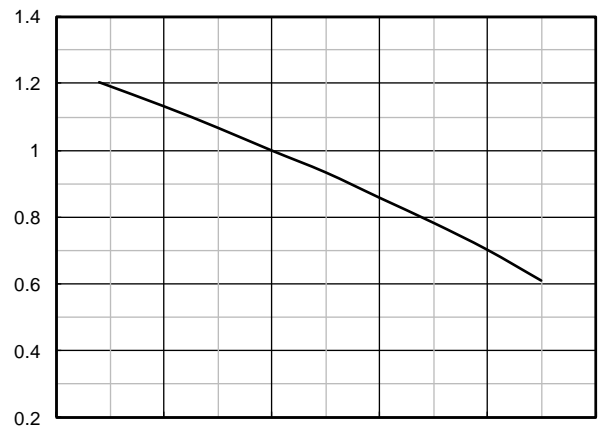


Figure 10. Normalized Threshold voltage

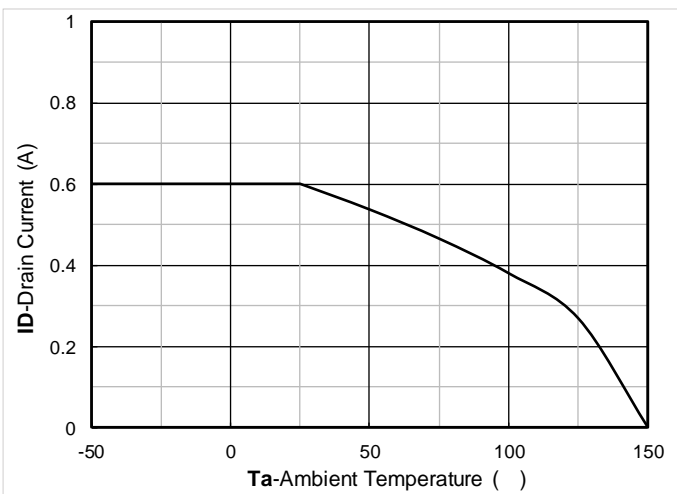


Figure 11. Current dissipation

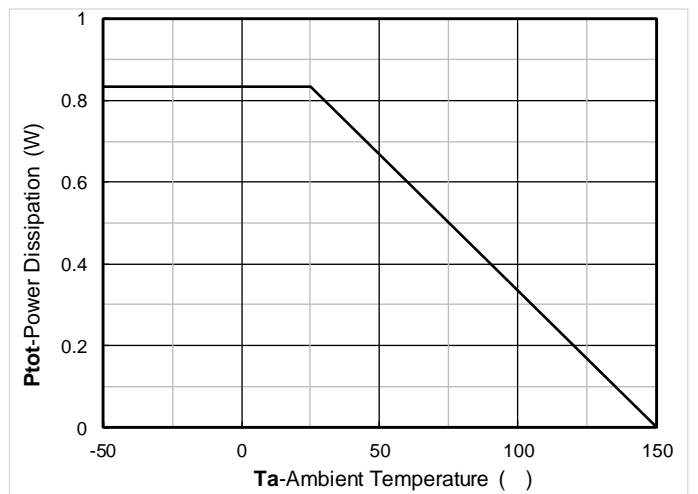


Figure 12. Power dissipation

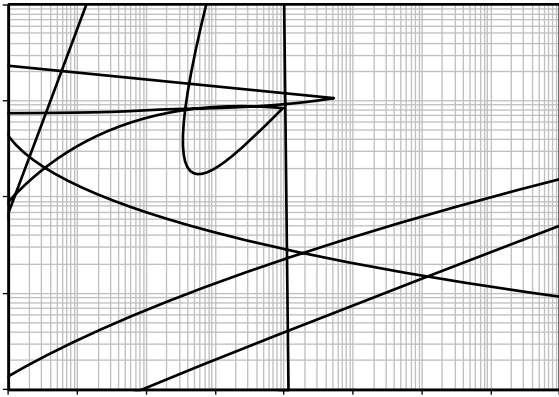


Figure 13. Maximum Transient Thermal Impedance

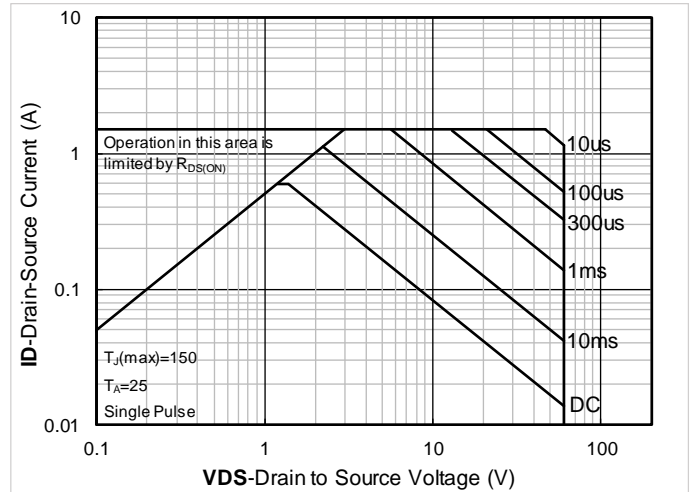


Figure 14. Safe Operation Area

## Test Circuits & Waveforms

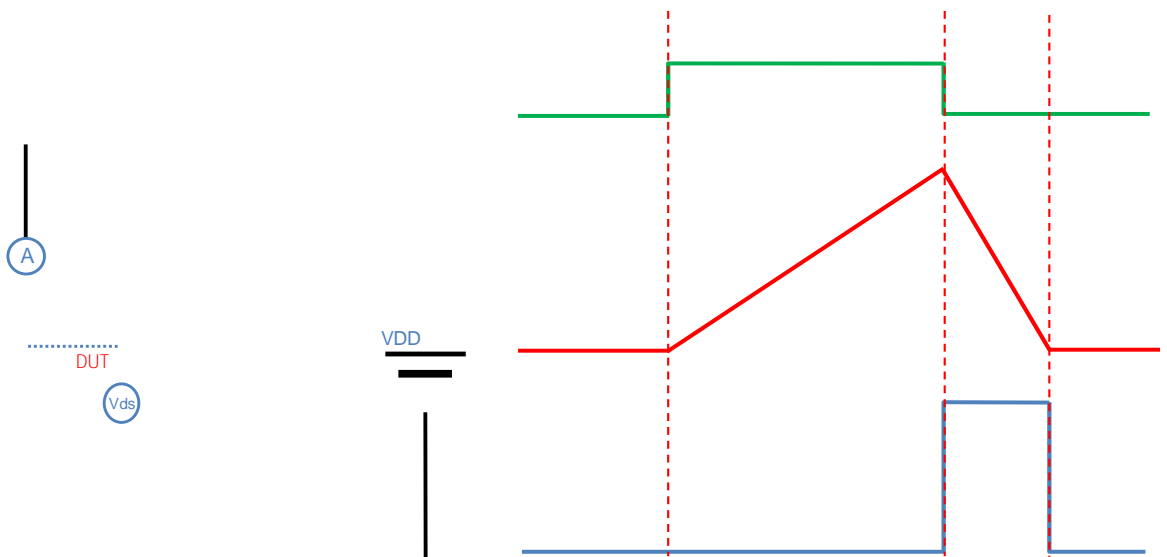


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

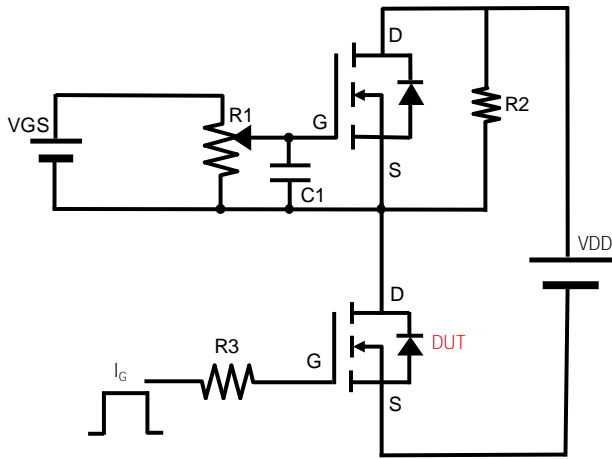


Figure B. Gate Charge Test Circuit & Waveform

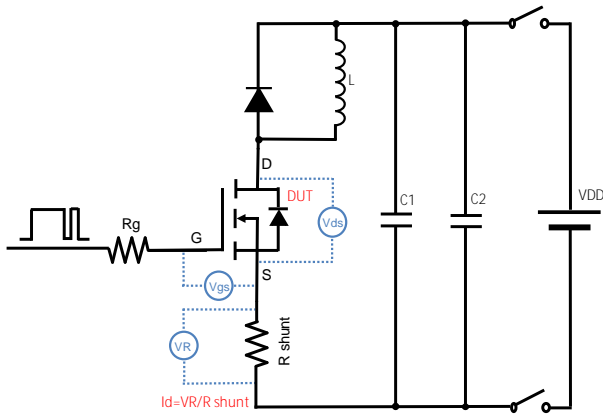


Figure C. Resistive Switching Test Circuit & Waveform

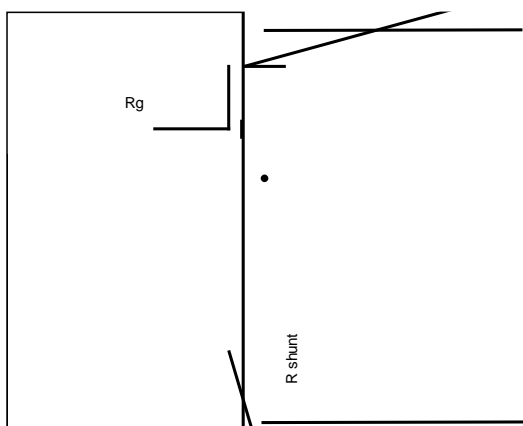
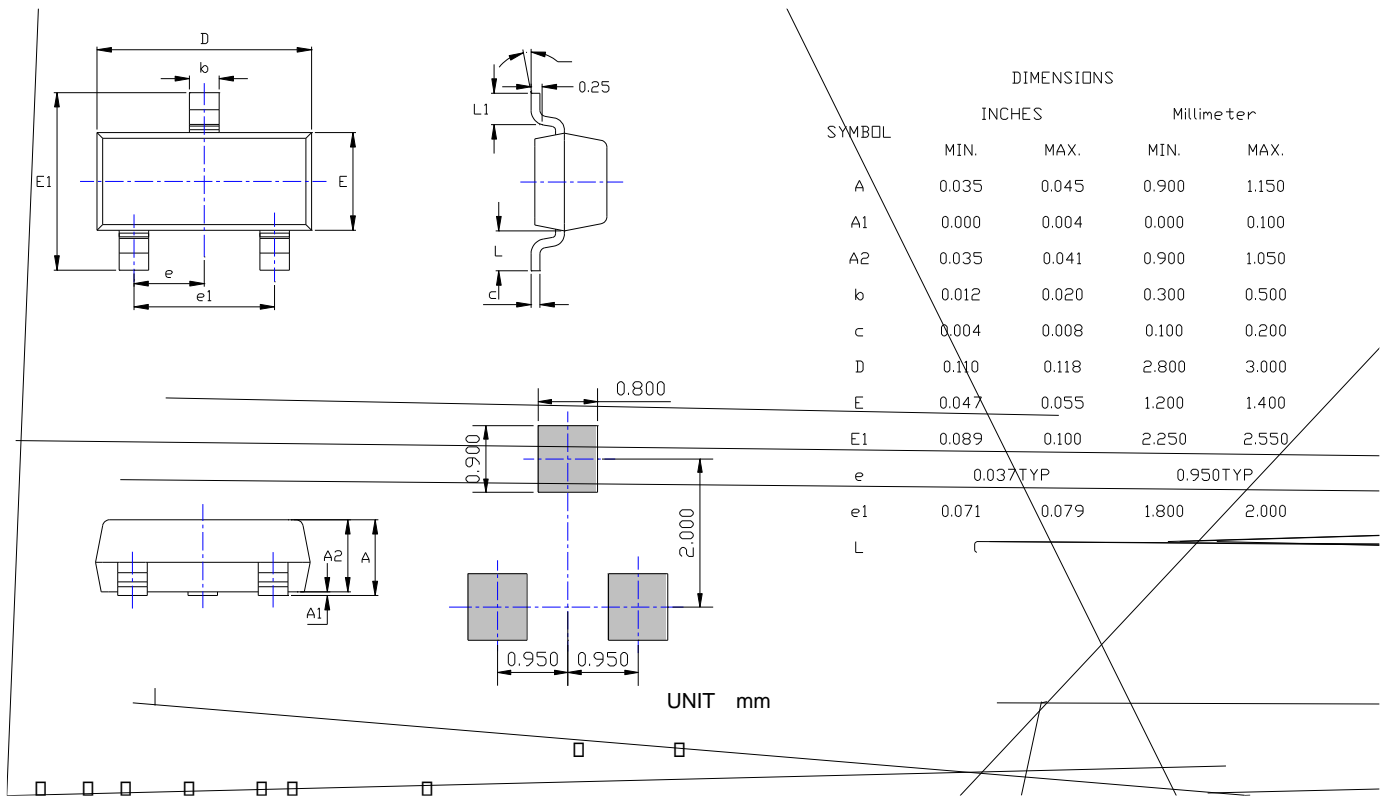


Figure D. Diode Recovery Test Circuit & Waveform



# BSS138KJ

## SOT-23 Package information





## BSS138KJ

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